Switch-mode Power Rectifier 45 V, 20 A

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- Guard-Ring for Stress Protection

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

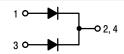
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube
- These Devices are Pb-Free and are RoHS Compliant*



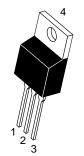
ON Semiconductor®

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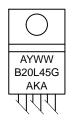
DUAL SCHOTTKY BARRIER RECTIFIERS 20 AMPERES, 45 VOLTS



MARKING DIAGRAMS

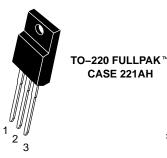


TO-220 CASE 221A STYLE 6



AYWW

B20L45G AKA



B20L45 = Device Code A = Assembly Location

Y = Year
WW = Work Week
AKA = Polarity Designator
G = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping
MBR20L45CTG	TO-220 (Pb-Free)	50 Units/Rail
MBRF20L45CTG	TO-220FP (Pb-Free)	50 Units/Rail

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	45	V
Average Rectified Forward Current (Rated V_R) $T_C = 141$ °C	I _{F(AV)}	10	А
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz)	I _{FRM}	20	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	180	А
Operating Junction Temperature (Note 1)	TJ	-55 to +150	°C
Storage Temperature	T _{stg}	-55 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic		Symbol	Value	Unit
Maximum Thermal Resistance				°C/W
(MBR20L45CTG)	Junction-to-Case	$R_{ heta JC}$	1.9	
	Junction-to-Ambient	$R_{ hetaJA}$	45	
(MBRF20L45CTG)	Junction-to-Case	$R_{ heta JC}$	2.2	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) $ \begin{aligned} &(I_F=10 \text{ A, } T_C=25^\circ\text{C}) \\ &(I_F=10 \text{ A, } T_C=125^\circ\text{C}) \\ &(I_F=20 \text{ A, } T_C=25^\circ\text{C}) \\ &(I_F=20 \text{ A, } T_C=125^\circ\text{C}) \end{aligned} $	VF	0.50 0.47 0.63 0.62	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^{\circ}C$) (Rated DC Voltage, $T_C = 125^{\circ}C$)	i _R	0.5 170	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{1.} The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

^{2.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2.0%.

TYPICAL CHARACTERISTICS

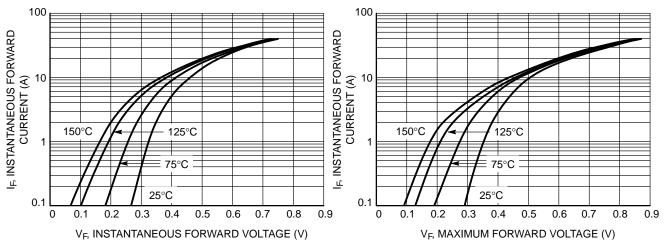


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

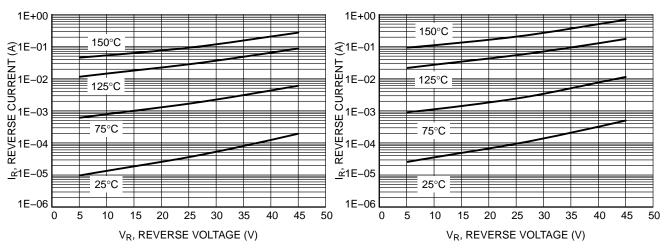


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

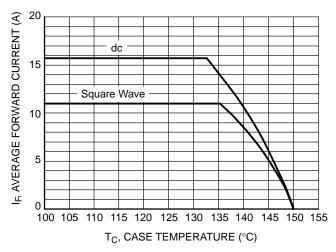


Figure 5. Current Derating

TYPICAL CHARACTERISTICS

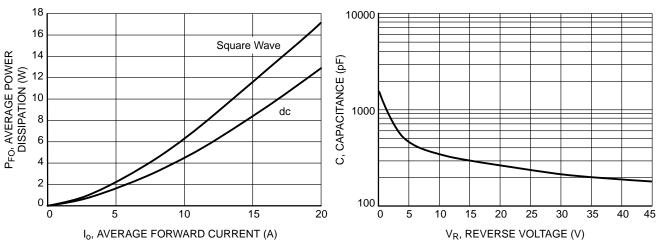


Figure 6. Forward Power Dissipation

Figure 7. Typical Capacitance

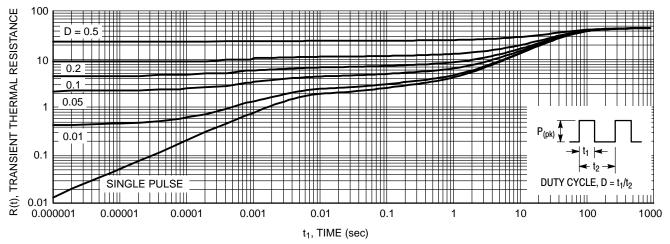


Figure 8. Thermal Response Junction-to-Ambient for MBR20L45CTG

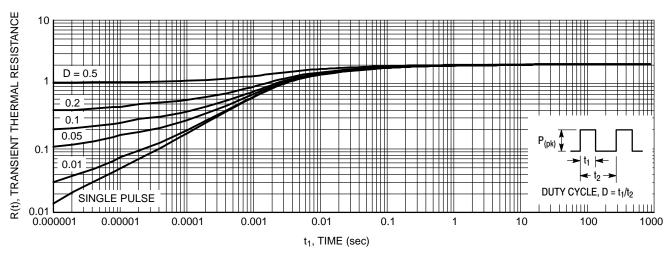


Figure 9. Thermal Response Junction-to-Case for MBR20L45CTG

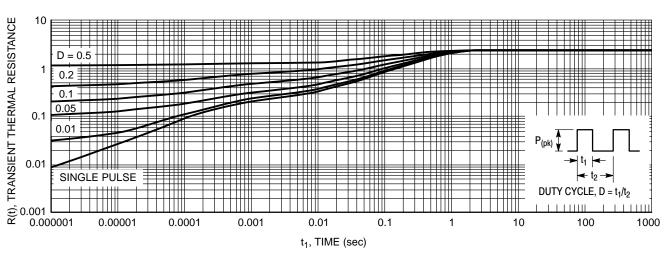
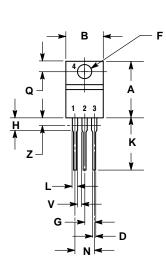
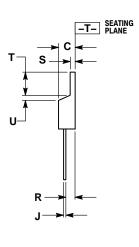


Figure 10. Thermal Response Junction-to-Case for MBRF20L45CTG

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

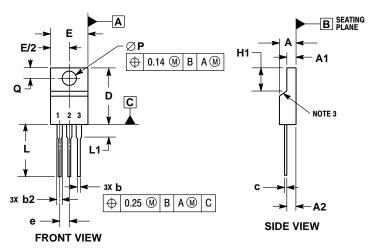
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
7		0.080		2 04

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

PACKAGE DIMENSIONS

TO-220 FULLPACK, 3-LEAD

CASE 221AH ISSUE F

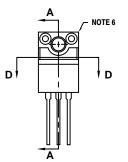


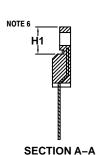
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR UNCONTROLLED IN THIS AREA.
- CONTOUR ONLOWINGLED IN THIS AREA
 ADMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
 DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
- DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
 LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
 CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY
- CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS AT AND H1 FOR MANUFACTURING PURPOSES.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.30	4.70	
A1	2.50	2.90	
A2	2.50	2.90	
b	0.54	0.84	
b2	1.10	1.40	
С	0.49	0.79	
D	14.70	15.30	
E	9.70	10.30	
е	2.54 BSC		
H1	6.60	7.10	
L	12.50	14.73	
L1		2.80	
P	3.00	3.40	
Q	2.80	3.20	







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